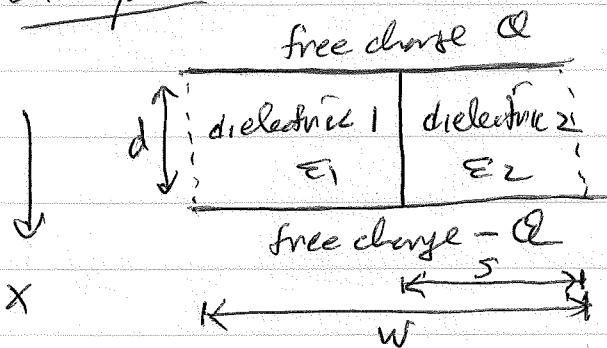


example



space between two conducting plates is filled with two dielectrics as shown

free charge $+Q$ on top plate
and $-Q$ on bottom plate.

We know the charge Q cannot be spread out uniformly

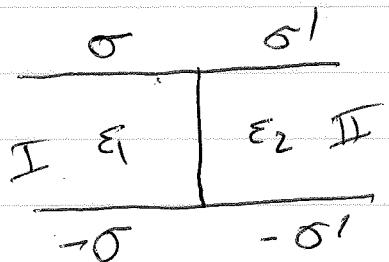
over the plates. If it was, with $\sigma_0 = Q/A$
then the electric field in dielectric 1 would be

$$\vec{E}_1 = \frac{\sigma_0}{\epsilon_1} \hat{x}$$
 and in dielectric 2 it would be $\vec{E}_2 = \frac{\sigma_0}{\epsilon_2} \hat{x}$

i.e. $\vec{E}_1 \neq \vec{E}_2$. But we must have

$-\int_0^d E \cdot dx = \Delta V$ the same on both sides (i.e. in both dielectrics 1 and 2) since the conducting plates must be at a constant potential

$\Rightarrow Q$ is not uniformly distributed over the plates



where $\sigma \neq \sigma'$ but

$$A \left[\sigma \left(\frac{w-s}{w} \right) + \sigma' \left(\frac{s}{w} \right) \right] = Q$$

in region I: $\vec{D} = \sigma \hat{x} \Rightarrow \vec{E}_1 = \frac{\sigma}{\epsilon_1} \hat{x}$

in region II: $\vec{D} = \sigma' \hat{x} \Rightarrow \vec{E}_2 = \frac{\sigma'}{\epsilon_2} \hat{x}$

Now we must have $\bar{E}_1 = \bar{E}_2 \Rightarrow \frac{\sigma}{\epsilon_1} = \frac{\sigma'}{\epsilon_2}$

$$\sigma' = \left(\frac{\epsilon_2}{\epsilon_1}\right)\sigma = \left(\frac{k_2}{k_1}\right)\sigma$$

Now we can find σ and σ'

$$\text{we had } A \left[\sigma \left(\frac{w-s}{w} \right) + \sigma' \left(\frac{s}{w} \right) \right] = Q$$

$$\sigma \left(\frac{w-s}{w} \right) + \frac{k_2}{k_1} \sigma \left(\frac{s}{w} \right) = \frac{Q}{A}$$

$$\sigma \left[\frac{w-s}{w} + \frac{k_2}{k_1} \frac{s}{w} \right] = \frac{Q}{A}$$

$$\sigma = \frac{Qw}{A} \frac{1}{w - s + \frac{k_2}{k_1} s}$$

$$= \frac{Qw}{A} \frac{1}{w + \left(\frac{k_2}{k_1} - 1\right)s}$$

$$\sigma' = \frac{k_2}{k_1} \sigma = \frac{Qw}{A} \frac{k_2}{k_1} \frac{1}{w + \left(\frac{k_2}{k_1} - 1\right)s}$$

We can now find the capacitance of this geometry

$$C = \frac{Q}{\Delta V}$$

$$\Delta V = E d = \frac{\sigma d}{\epsilon_1}$$

$$C = \frac{Q \epsilon_1}{\sigma d} = \frac{Q \epsilon_1}{d} \frac{A (w + \left(\frac{k_2}{k_1} - 1\right)s)}{Qw}$$

$$C = \frac{A}{d} \epsilon_1 \left(\frac{w + (\frac{\kappa_2}{\kappa_1} - 1)s}{w} \right)$$

$$= \frac{A}{d} \epsilon_1 \left(1 - \frac{s}{w} \right) + \frac{A}{d} \epsilon_1 \frac{\kappa_2}{\kappa_1} \frac{s}{w} \quad \frac{\kappa_2}{\kappa_1} = \frac{\epsilon_2}{\epsilon_1}$$

$$= \frac{A}{d} \epsilon_1 \left(\frac{w-s}{w} \right) + \frac{A}{d} \epsilon_2 \left(\frac{s}{w} \right)$$

$$= C_1 + C_2$$

where C_1 is capacitance from dielectric 1, C_2 is capacitance from dielectric 2

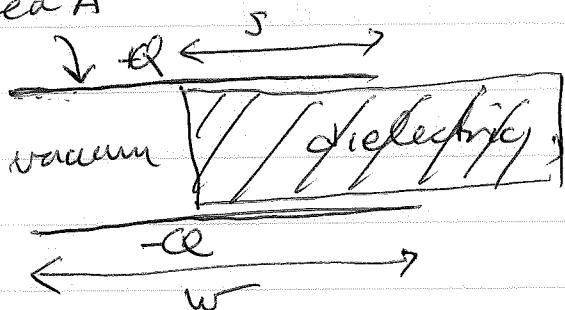
$A(\frac{w-s}{w})$ is area covered by ϵ_1

$A(\frac{s}{w})$ is area covered by ϵ_2

Forces on dielectrics

- just like we saw that a conductor is attracted to charge due to the induced charges in the conductor, so also a dielectric is attracted to free charge due to the bound charge created by the polarization of the dielectric

area A



dielectric inserted a distance s into the gap of a parallel plate capacitor of width w . Charges $+Q$ on top plate, $-Q$ on bottom plate.

we get the capacitance of this configuration from the last problem

$$C = C_{\text{vac}} \left(\frac{w-s}{s} \right) + C_{\text{dielec}} \left(\frac{s}{w} \right)$$

$$= \frac{A \epsilon_0}{d} \left(\frac{w-s}{s} \right) + \frac{A \epsilon}{d} \left(\frac{s}{w} \right)$$

$$= \frac{A \epsilon_0}{dw} (w - s + ks)$$

$$k-1 = \chi_e$$

$$= \frac{A \epsilon_0}{dw} (w + \chi_e s)$$

keep Q fixed, vary s

charge in energy is

$$\frac{dW}{ds} = \vec{F} = -\vec{F}_e$$

↑
Change in work
we do to vary s

↑
force we exert

electrostatic
force on dielectric

$$F_e = -\frac{dW}{ds} \Big|_{\text{at constant } Q}$$

use $W = \frac{1}{2} \frac{Q^2}{C}$

$$F_e = -\frac{1}{2} Q^2 \frac{d}{ds} \left(\frac{1}{C} \right) = \frac{1}{2} \frac{Q^2}{C^2} \frac{dC}{ds}$$

$$= \frac{1}{2} \frac{Q^2}{C^2} \frac{A \epsilon_0}{dW} \chi_e$$

$$= \frac{1}{2} (\Delta V)^2 \epsilon_0 \chi_e \frac{A}{dW}$$

use $C = \frac{Q}{\Delta V}$ so

$$\Delta V = \frac{Q}{C}$$

ΔV is voltage drop
between the charged plates

$$F_e = -\frac{dW}{ds} > 0$$

\Rightarrow as s increases, W decreases

we lower the energy by putting more dielectric
in between the plates.

$\Rightarrow F_e$ pulls dielectric into the plates

We could instead have done the calculation keeping the
potential drop ΔV constant, rather than keeping
 Q constant. But as s changes for constant ΔV ,
the total charge Q on the plates must change
since $Q = C \Delta V$ and C changes. To keep V
constant, the battery must do work by adding
the necessary ΔQ as s varies.

Note: $\epsilon_0 \chi_e = \epsilon - \epsilon_0$ so we can write

$$F_e = \frac{1}{2} \frac{(\Delta V)^2}{W} (C - C_0) \quad \text{where } C = \frac{AB}{d}, C_0 = \frac{A \epsilon_0}{d}$$

$$F_e = -\frac{dW}{ds} + \Delta V \frac{d(Q)}{ds}$$

T
 electrostatic
 energy \uparrow
 work done
 by the battery

use $W = \frac{1}{2} (\Delta V)^2 C$ $C = \frac{Q}{\Delta V}$

$$F_e = -\frac{1}{2} (\Delta V)^2 \frac{dC}{ds} + \Delta V \frac{d}{ds}(\Delta V C)$$

$$= -\frac{1}{2} (\Delta V)^2 \frac{dC}{ds} + (\Delta V)^2 \frac{dc}{ds}$$

$$= \frac{1}{2} (\Delta V)^2 \frac{dc}{ds}$$

$$= \frac{1}{2} (\Delta V)^2 \frac{A \epsilon_0 \chi e}{dw}$$

same result as before
 so force is the same
 whether we keep charge Q ,
 or potential drop ΔV , constant

4.11

Susceptibility and Atomic Polarizability

$\vec{P} = \alpha \vec{E}_{loc}$ where \vec{E}_{loc} is the local electric field acting on an atom that polarizes it.
 \vec{E}_{loc} is due to all sources other than the charge of the atom itself.

$$\vec{P} = N\vec{p} = N\alpha \vec{E}_{loc} \quad N = \text{density of atoms}$$

If $\vec{E}_{loc} = \vec{E}$, the average electric field, then we would have

$$\vec{P} = N\vec{p} = N\alpha \vec{E} = \epsilon_0 \chi_e \vec{E}$$

$$\Rightarrow \chi_e = \frac{N\alpha}{\epsilon_0} \quad \begin{matrix} \text{relates macroscopic } \chi_e \\ \text{to microscopic } \alpha \end{matrix}$$

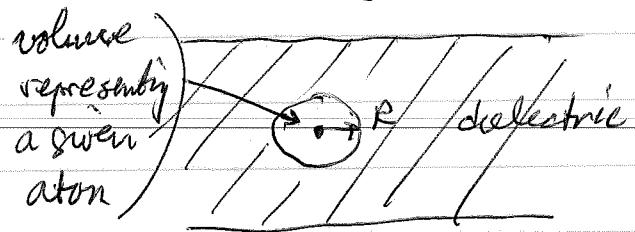
BUT $\vec{E} \neq \vec{E}_{loc}$ as \vec{E} includes the electric field produced by the atom itself.

$$\vec{E} = \vec{E}_{loc} + \vec{E}_{atom}$$

↑ average field due to the atom,

Let us take the volume per atom to be a sphere of radius R such that $\frac{4}{3}\pi R^3 = 1/N$

Let us say that an average thin sphere, representing the portion of the system belonging to a given atom, is uniformly polarized with polarization \vec{P} .



Then the average field from the atom inside this sphere would be

$$\vec{E}_{atom} = -\frac{\vec{P}}{3\epsilon_0}$$

field inside a uniformly polarized sphere

Now $\frac{4\pi R^3}{3} \vec{P} = \vec{p}$ the total dipole moment on the sphere
 = total dipole moment on atom

$$\vec{p} = \alpha \vec{E}_{loc}$$

$$\Rightarrow \vec{P} = \frac{3\alpha \vec{E}_{loc}}{4\pi R^3}$$

average full $\vec{E} = \vec{E}_{loc} + \vec{E}_{atom} = \vec{E}_{loc} - \frac{\vec{P}}{3\epsilon_0} = \vec{E}_{loc} - \frac{\alpha \vec{E}_{loc}}{4\pi \epsilon_0 R^3}$

$$\vec{E} = \left(1 - \frac{\alpha}{4\pi \epsilon_0 R^3}\right) \vec{E}_{loc}$$

$$\vec{P} = N \vec{p} = N \alpha \vec{E}_{loc} = \frac{N\alpha}{1 - \frac{\alpha}{4\pi \epsilon_0 R^3}} \vec{E}$$

Now $\frac{4\pi R^3}{3} = 1/N$ so

$$\vec{P} = \frac{N\alpha}{1 - \frac{N\alpha}{3\epsilon_0}} \vec{E} \Rightarrow$$

$$\epsilon_0 \chi_e = \frac{N\alpha}{1 - \frac{N\alpha}{3\epsilon_0}}$$

If density N is sufficiently small, we can regard the denominator as unity and regain $\epsilon_0 \chi_e = N\alpha$ that we found when we assumed $E = E_{loc}$. The above thus gives the correction to this small N limit.

$$\chi_e = \frac{N\alpha/\epsilon_0}{1 - \frac{N\alpha}{3\epsilon_0}}$$

If a is the radius of the actual atom ($a \sim \text{\AA}$) then we can define

$$f = \frac{\frac{4\pi a^3}{3}}{\frac{4\pi R^3}{3}} = \frac{4\pi a^3}{3} N$$

f is just the fraction of the space of the dielectric that is occupied by the atoms (the rest is just the empty space between atoms)

$$\chi_e = \frac{Nd/\epsilon_0}{1 - Nd/3\epsilon_0}$$

If we use our simple model of atomic polarizability that we discussed at the start of our section on dielectrics, then we have

$$\alpha = 4\pi\epsilon_0 a^3$$

\Rightarrow

$$\chi_e = \frac{4\pi a^3 N}{1 - \frac{4}{3}\pi a^3 N} = \boxed{\frac{3f}{1-f} = \chi_e}$$

Claussius
- Mossotti
equation

In terms of the dielectric constant $\kappa = 1 + \chi_e$
we can write

$$\chi_e = \frac{Nd/\epsilon_0}{1 - Nd/\epsilon_0} \Rightarrow \chi_e - \frac{N\kappa}{3\epsilon_0} \chi_e = \frac{N\kappa}{\epsilon_0}$$

$$\Rightarrow \chi_e = \frac{N}{\epsilon_0} \left(1 + \frac{\chi_e}{3}\right) \alpha$$

$$\Rightarrow \alpha = \frac{\epsilon_0}{N} \frac{\chi_e}{1 + \frac{\chi_e}{3}} = \frac{3\epsilon_0}{N} \frac{\chi_e}{3 + \chi_e}$$

$$\boxed{\alpha = \frac{3\epsilon_0}{N} \left(\frac{\kappa-1}{\kappa+2}\right)}$$

Lorentz-Lorenz equation

Relates microscopic parameter α to macroscopic parameter κ .